

ABSTRACT

Since improvement measures are not taken in regard to the electrostatic breakdown voltage, electrostatic breakdown voltages, between the common input terminal IN –first control terminal Ctl-1, between the common input terminal IN - second control terminal Ctl-2, between the first control terminal Ctl-1 – the first output terminal OUT1, and between the second control terminal Ctl-2 – the second output terminal OUT2, where both ends of gate Schottky junctions of FETs are lead out to the exterior, are low. To solve the problem, the embodiment of the invention provides a switch circuit device, wherein protecting elements are connected by disposing two electrode pads, for connection to a single control terminal, on a chip and positioning the electrode pads near the common input terminal pad I and an output terminal pad O1 or O2. The electrostatic energies that are applied between the first output terminal OUT1 – the first control terminal Ctl-1, between the common input terminal IN – the first control terminal Ctl-1, between the second output terminal OUT2 – the second control terminal Ctl-2, and between the common input terminal IN – the second control terminal Ctl-2 can be respectively attenuated to the same degree and most efficiently.